



SSCN2412GS6

High Frequency High Gain NPN Power BJT

➤ Features

VCB	VCE	VEB	IC
60V	50V	7V	150mA

➤ Description

This product is general usage and suitable for many different applications. It can be used for medium power amplifiers and switches requiring collector currents up to 150 mA.

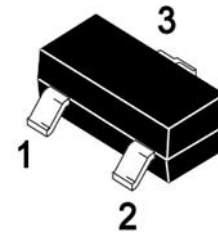
➤ Applications

- Low current and high precision circuits such preamplifiers, oscillators, current mirror configuration
- Medium power amplification and switching

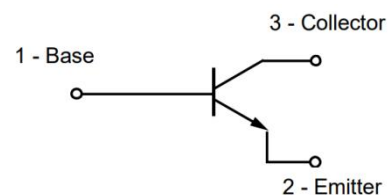
➤ Ordering Information

Device	Package	Shipping
SSCN2412GS6	SOT-23	3000/Reel

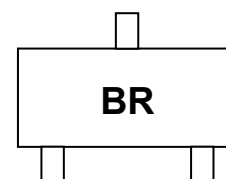
➤ Pin configuration



SOT-23



Circuit Diagram



Marking(Top View)



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

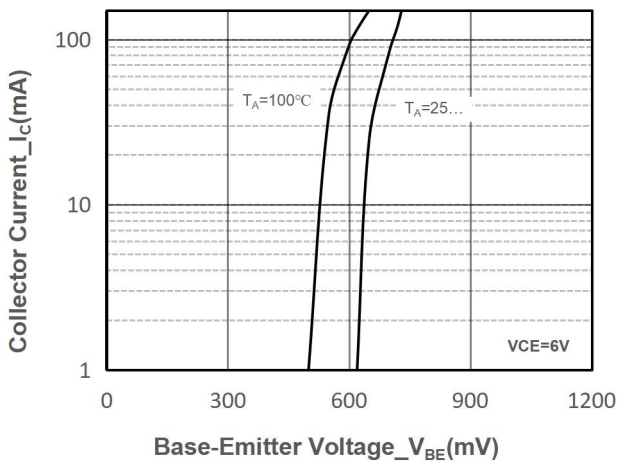
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	60	V
Collector- Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current-Continuous	I_C	150	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	-55 to 150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}\text{C}$

➤ **Electrical Characteristics** ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

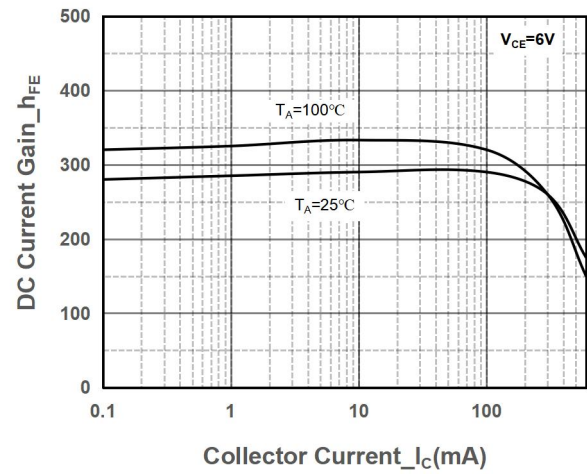
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 50\mu\text{A}$, $I_E = 0$	60			V
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C = 1\text{mA}$, $I_B = 0$	50			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E = 50\mu\text{A}$, $I_C = 0$	7			V
Collector Cutoff Current	I_{CB0}	$V_{CB} = 60\text{V}$, $I_E = 0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 7\text{V}$, $I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$	180		390	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}$, $I_B = 5\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE} = 12\text{V}$, $I_C = -2\text{mA}$ $F = 100\text{MHz}$		160		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 12\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		2.0	3.5	pF



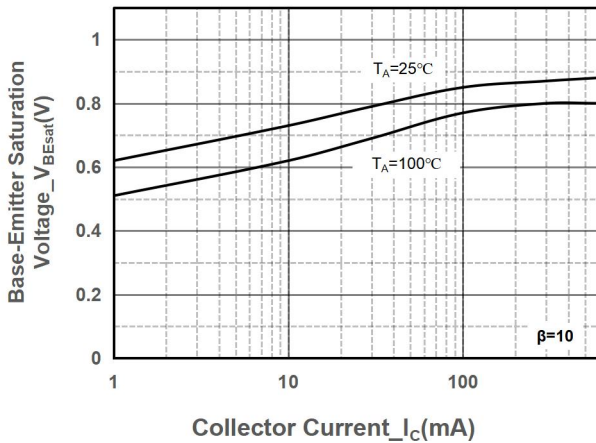
➤ Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)



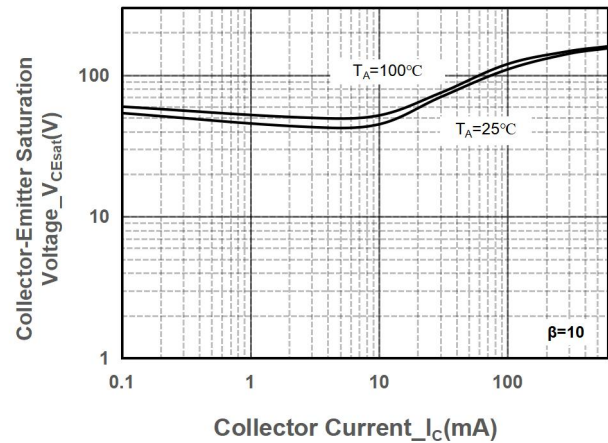
Collector Current vs. Base-Emitter Voltage



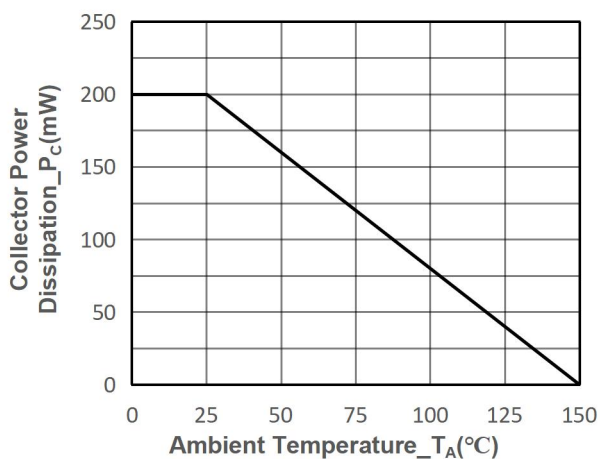
DC Current Gain vs. Collector Current



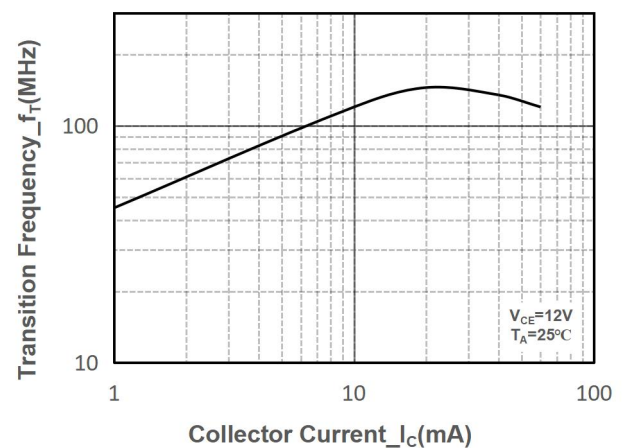
$V_{BE(sat)}$ vs. Collector Current



$V_{CE(sat)}$ vs. Collector Current



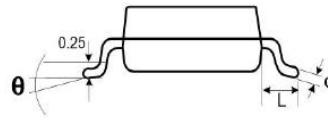
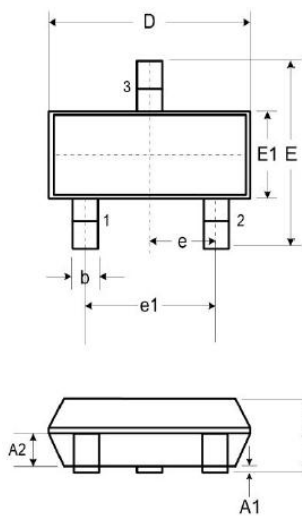
Power derating vs. Ambient temperature



Transition Frequency vs. Collector Current

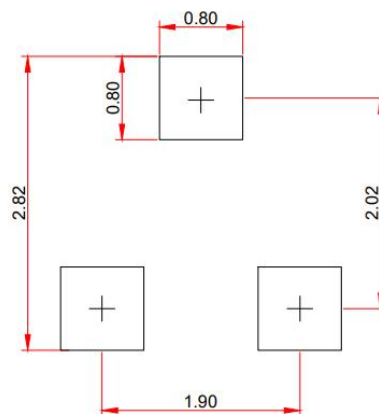


● Package Information



DIM	Millimeters		
	Min.	Typ.	Max.
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.51
c	0.08	-	0.18
D	2.80	2.90	3.04
E	2.10	2.37	2.64
E1	1.20	1.30	1.40
e	0.95		
e1	1.80		2.00
L	0.40	0.50	0.60
L1	0.30		0.50
θ	0°	-	8°

Recommended Pad outline(Unit: mm)





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